



N-channel Enhancement Mode Mosfet

CX3426B

DESCRIPTION

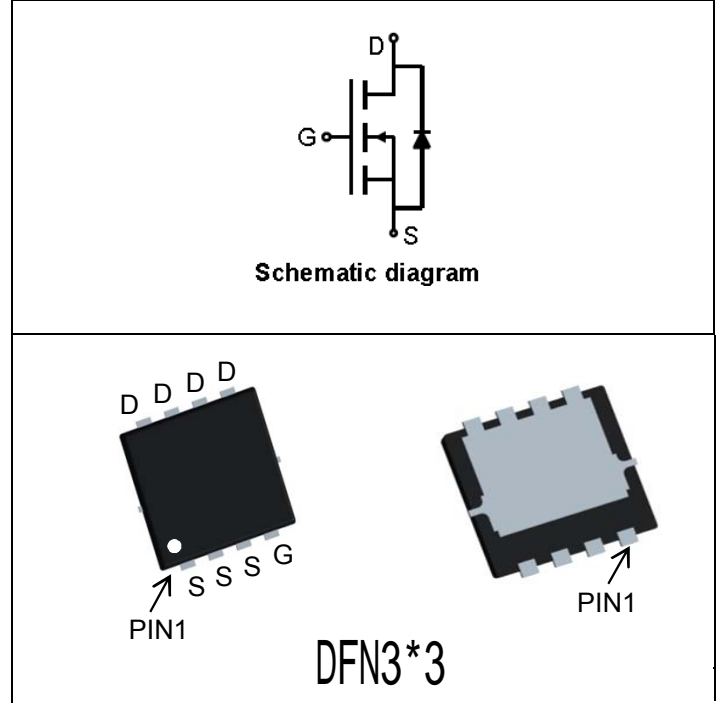
The CX3426 uses advanced trench technology to provide excellent RDS(ON) and low gate charge. This device is suitable for use as a load switch or in PWM applications.

GENERAL FEATURES

- RDS(ON) < 13mΩ @ VGS=4.5V
RDS(ON) < 10mΩ @ VGS=10V
- High Power and current handing capability
- Lead free product is acquired
- Surface Mount Package

Application

- PWM applications
- Load switch
- Power management



■ Absolute Maximum Ratings (T_A=25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		V _{DS}	30	V
Gate-source Voltage		V _{GS}	±20	V
Drain Current	T _C =25°C	I _D	30	A
	T _C =100°C		21	
Pulsed Drain Current ^A		I _{DM}	100	A
Total Power Dissipation	T _C =25°C	P _D	25	W
	T _C =100°C		10	W
Single Pulse Avalanche Energy ^B		E _{AS}	128	mJ
Thermal Resistance Junction-to-Case ^C		R _{θJC}	7.5	°C/W
Junction and Storage Temperature Range		T _J , T _{STG}	-55~+175	°C